

FIG. 1

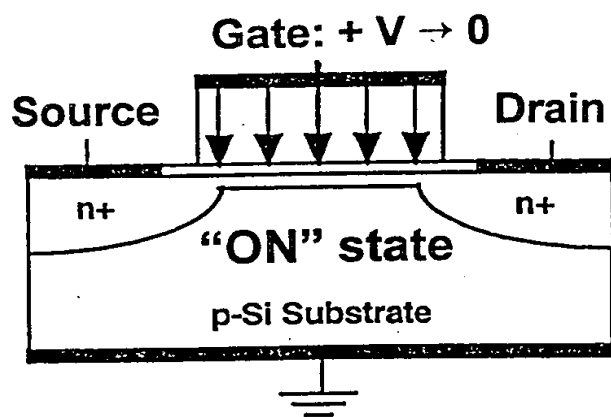


FIG. 2

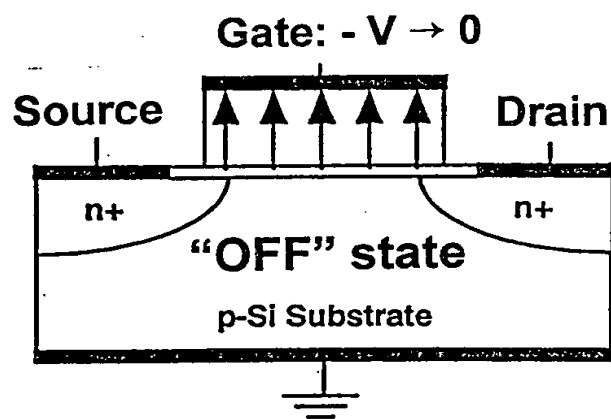


FIG. 3

000001 02241200

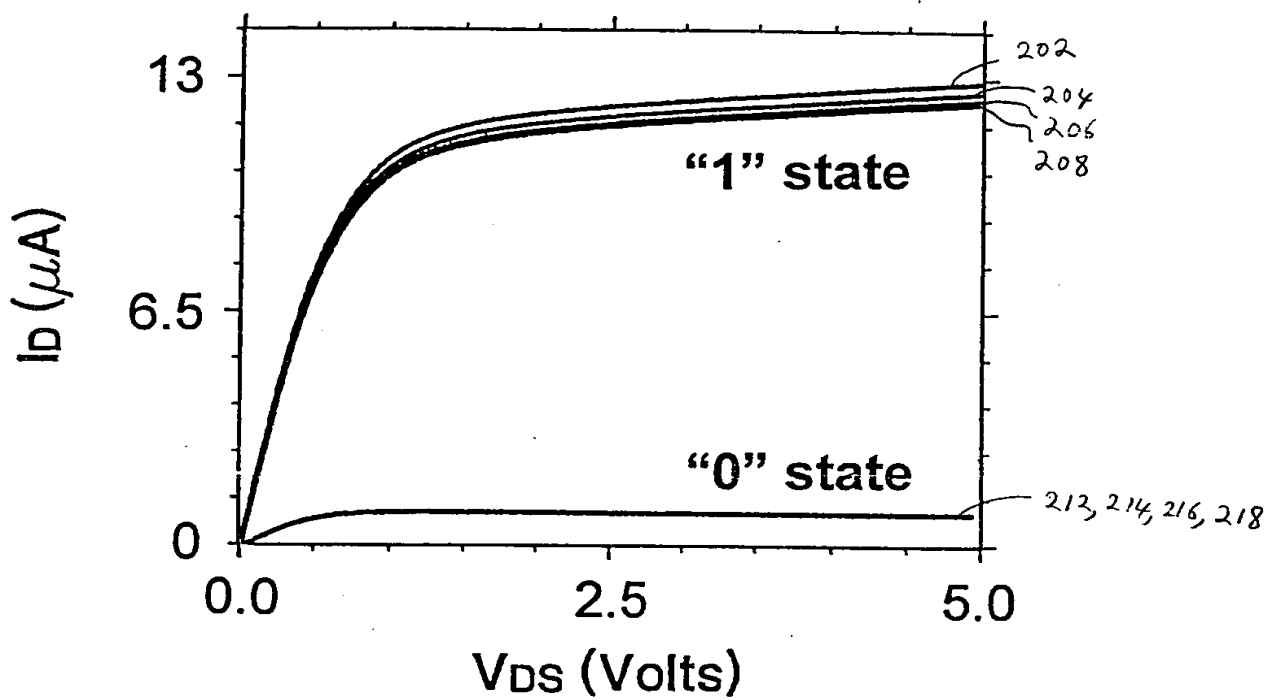


FIG. 4

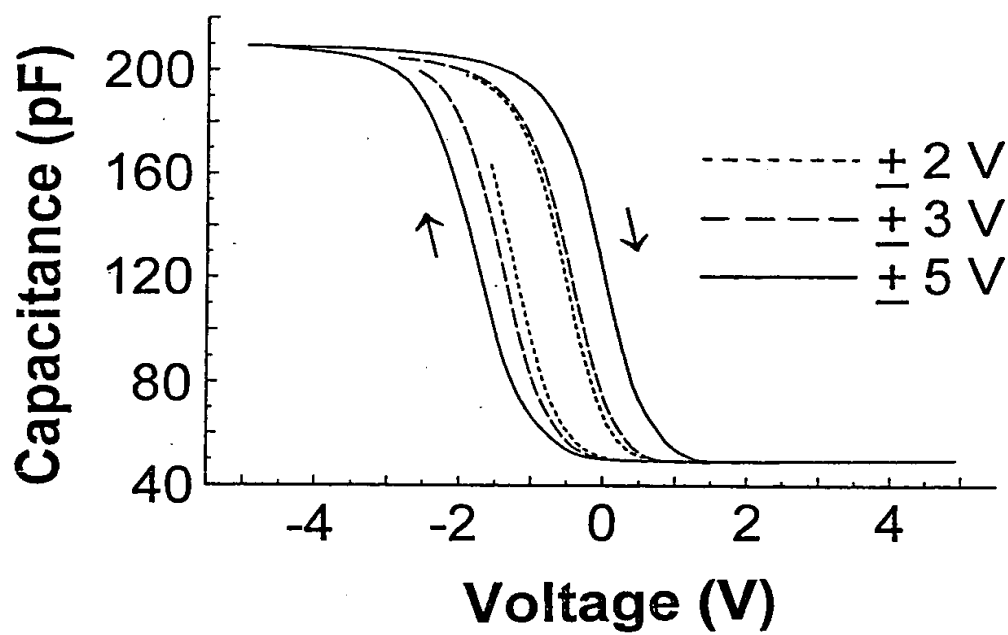


Fig. 5

300

p-Si substrate

A cross-sectional view of a semiconductor device. It shows a p-Si substrate (300) and a pad oxide layer (302) on top of it.

A cross-sectional view of a semiconductor device. A thick, dark, textured layer labeled "Silicon Nitride" covers the top surface. Below this layer is a lighter, uniform layer. The bottom of the device is a solid black layer. On the left side, there are three horizontal tick marks with labels: "304" at the top, "302" in the middle, and "300" at the bottom.

Fig. 8

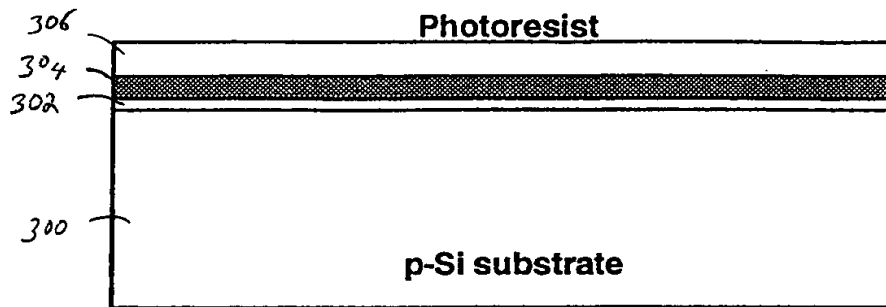


FIG. 9

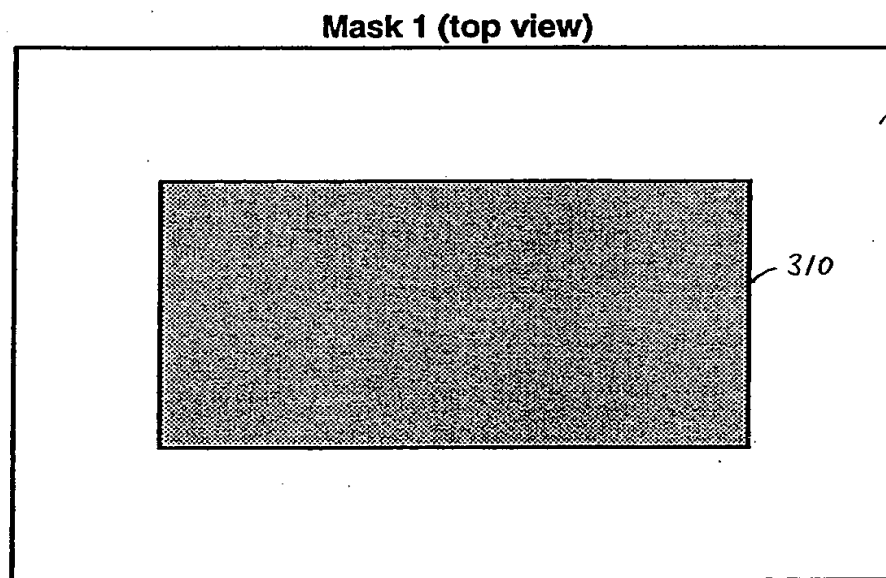


FIG. 10A

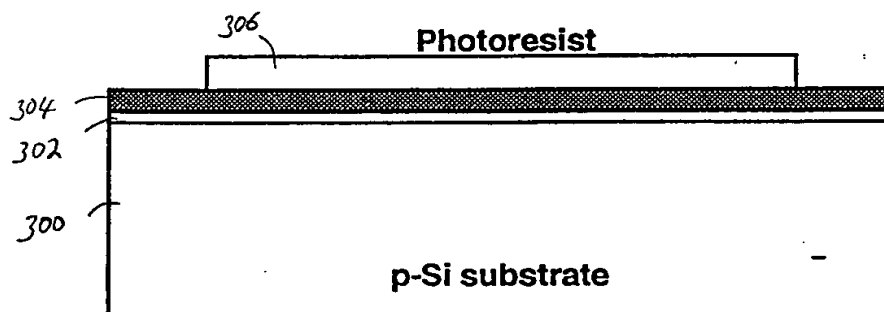
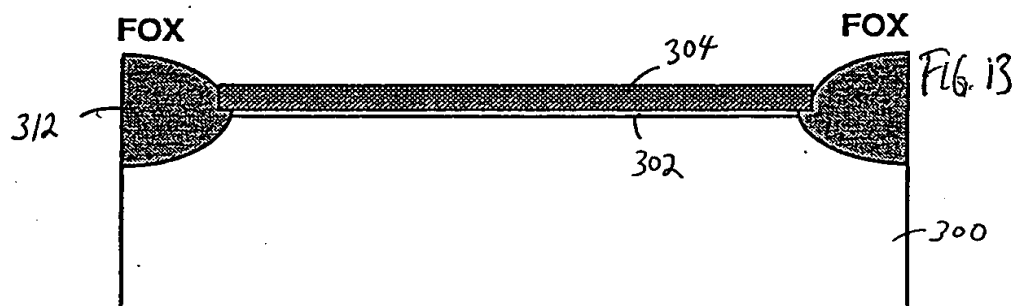
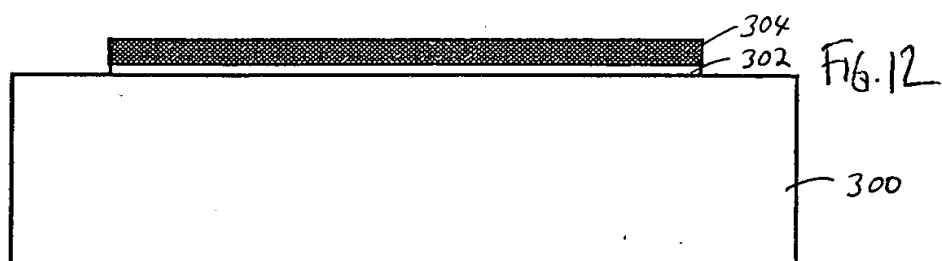
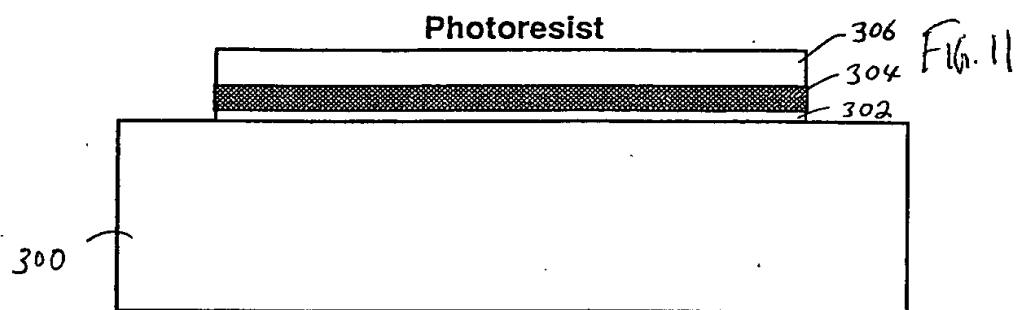
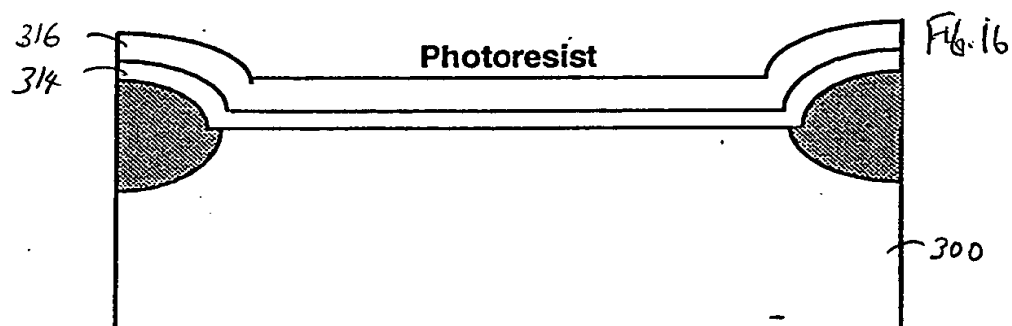
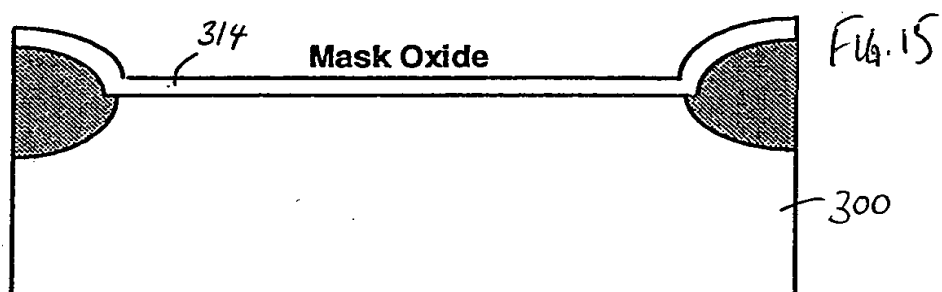
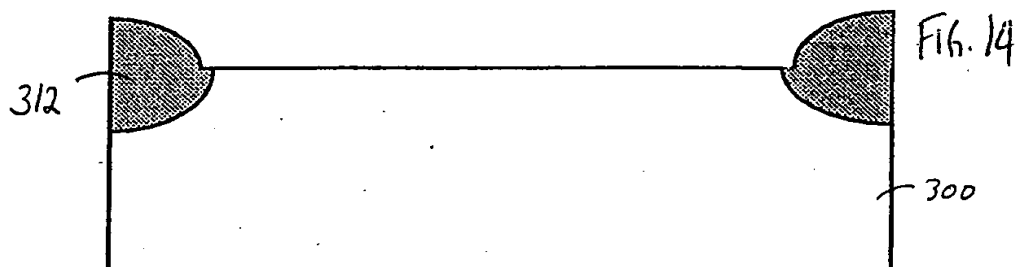


FIG. 10B

000001-000000

[illegible]



002227 00000000

Mask 2 (top view)

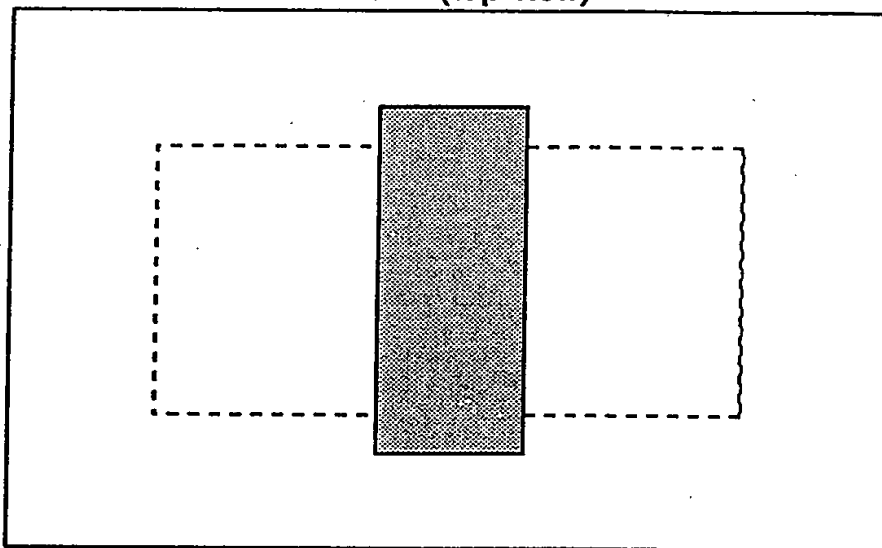


FIG. 17A

318

Photoresist

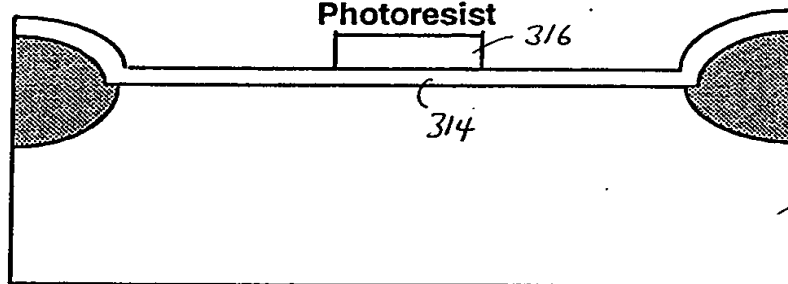


FIG. 17 B

300

Mask Oxide

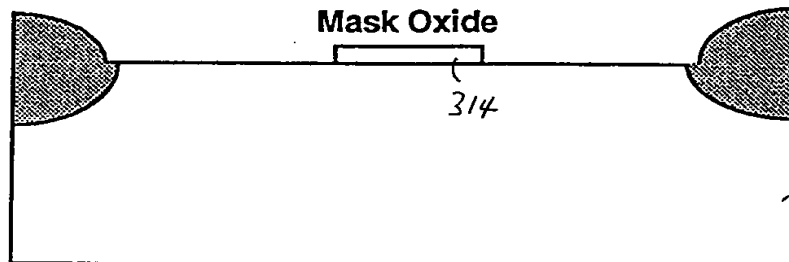
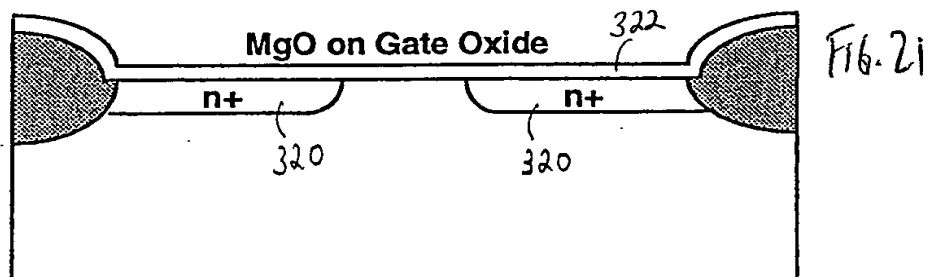
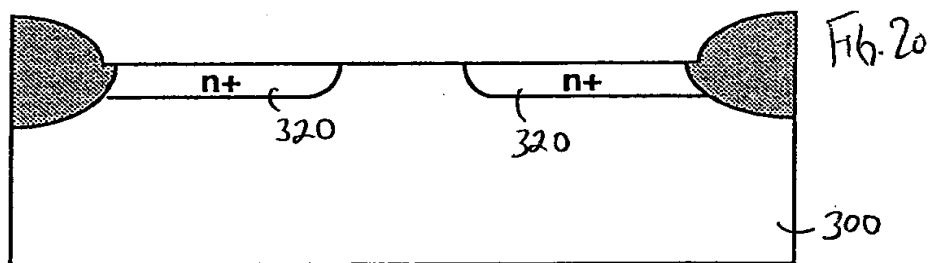
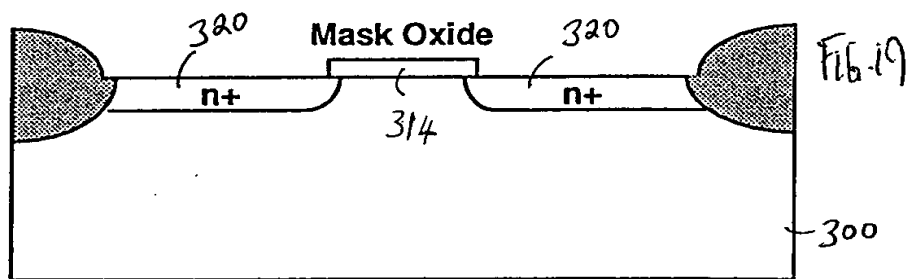


FIG. 18

300

000001-000000



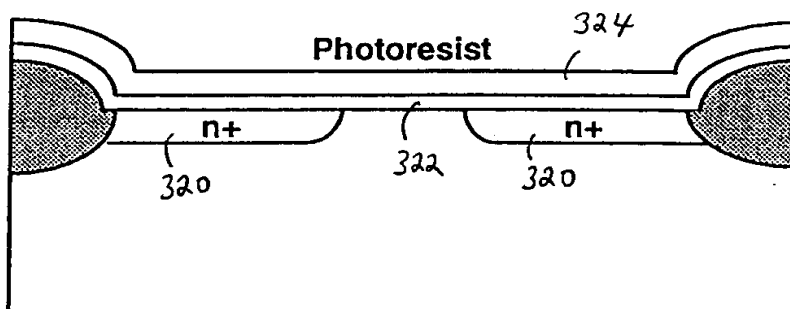


Fig. 22

Mask 3 (top view)

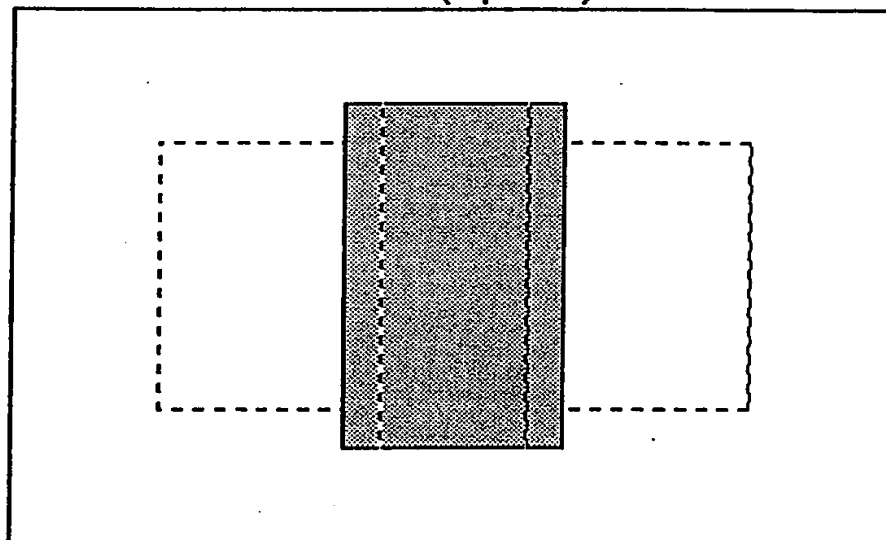


FIG. 23A

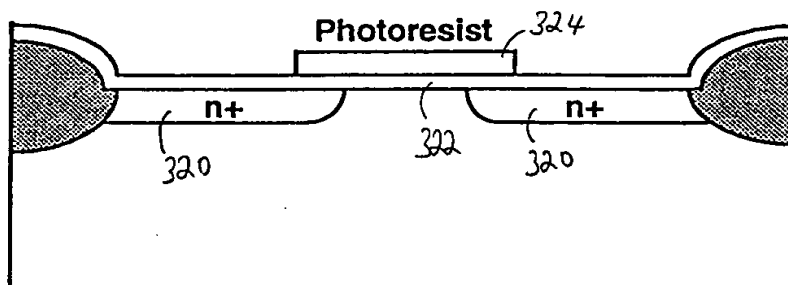


Fig. 23 B

000001 022460

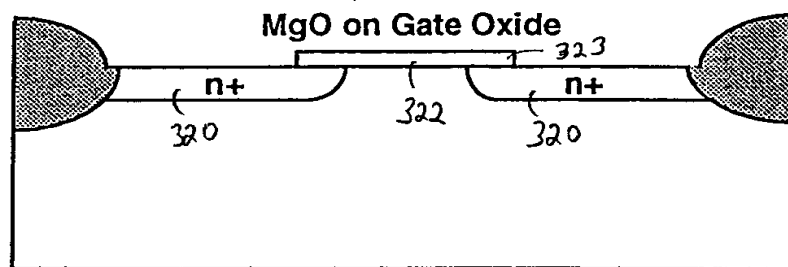


Fig. 24

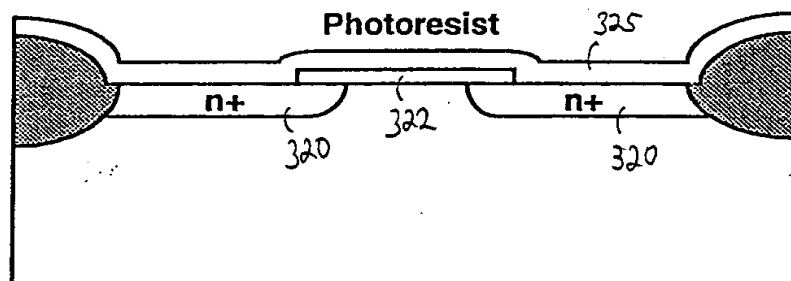


Fig. 25

Mask 4 (top view)

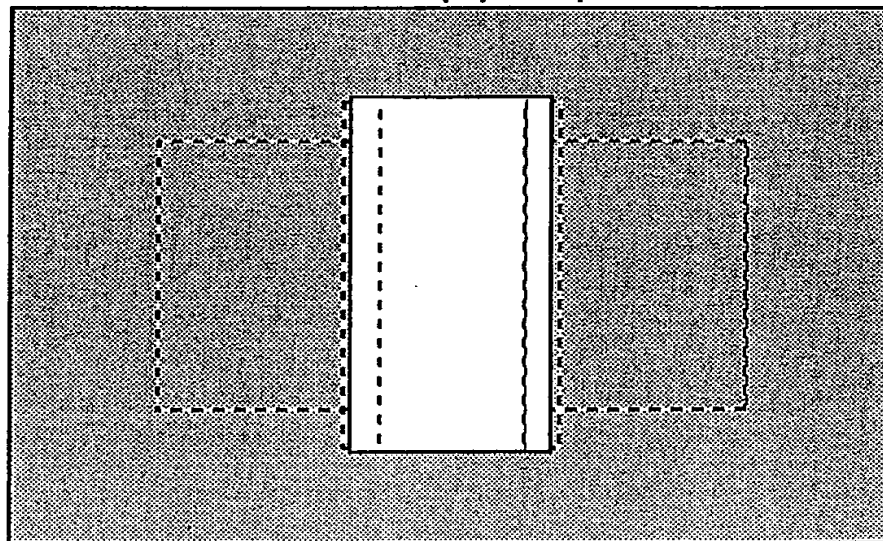
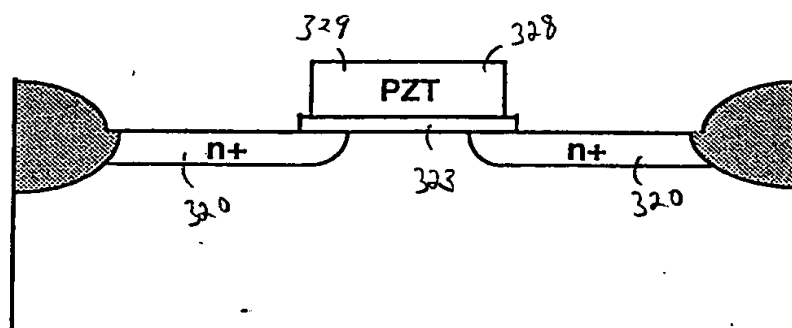
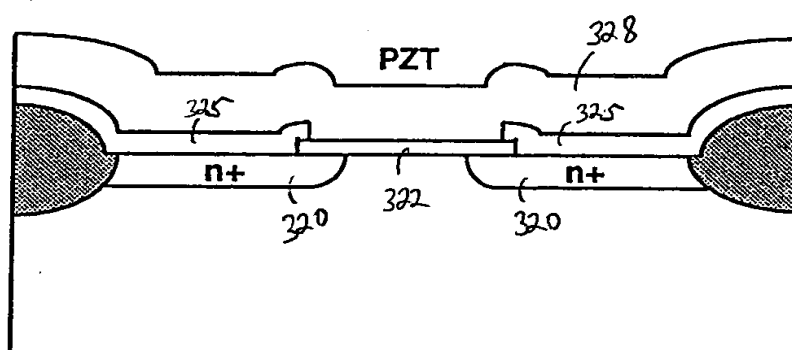
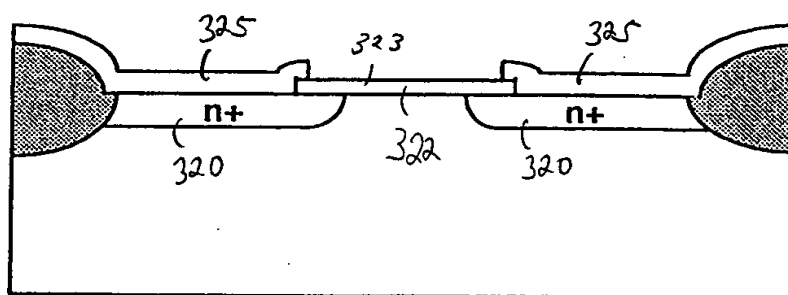
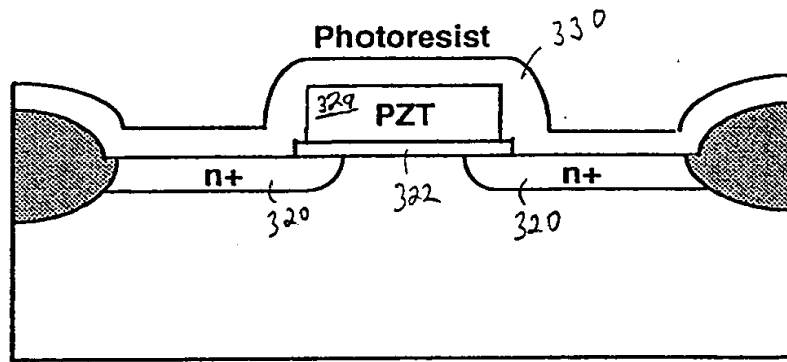
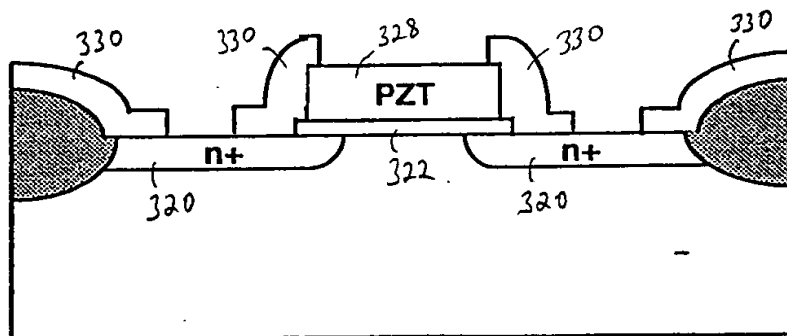
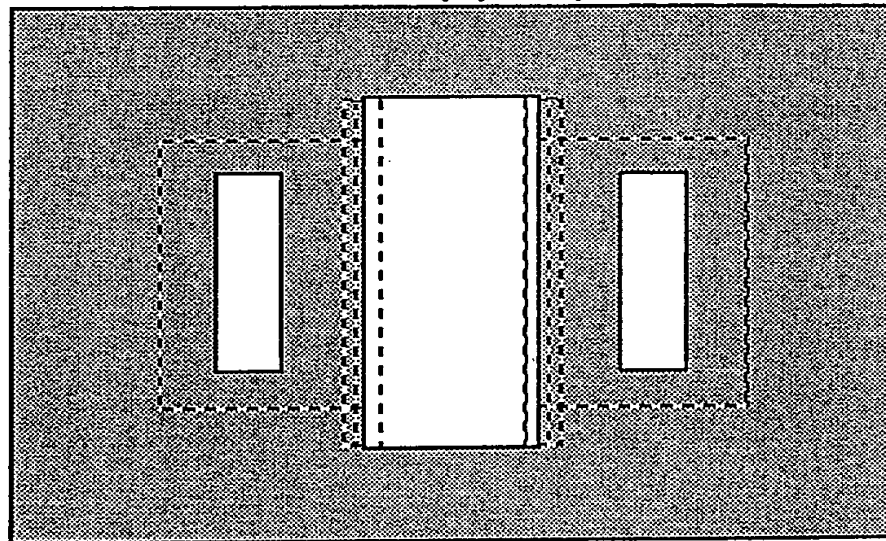


FIG. 26A





Mask 5 (top view)



The diagram shows a cross-section of a device. At the base is a **p-Si substrate**. Above it is a layer of **MgO on Gate Oxide**. A central **PZT** layer is positioned on top of the MgO. The PZT layer is flanked by two **n+** regions, labeled **336** and **340**. Above the PZT layer is a thin layer labeled **338**. The entire structure is capped with **FOX** (field oxide) on the left and right sides.

Fig. 32

000001-000001

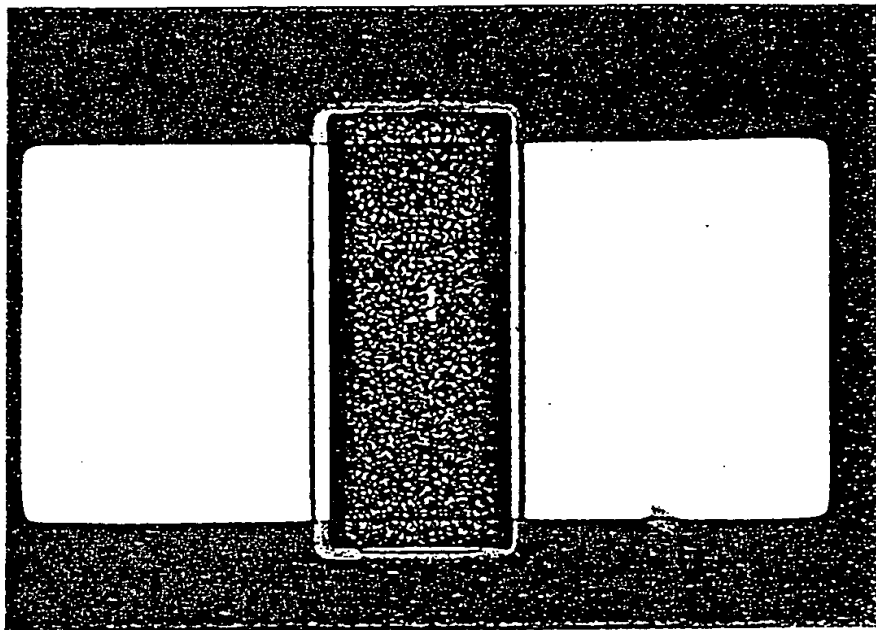


FIG. 33